

IN THE SPECIFICATION

Please amend the Specification as follows:

From the preliminary amendment filed on 12/12/2003, please amend the new section heading and paragraph added on page 2 as follows:

"CROSS-REFERENCE TO RELATED APPLICATION

This non-provisional United States (U.S.) patent application claims the benefit [[of]] and is a divisional application of U.S. Patent Application No. 10/119,594 filed on April 04, 2002 by inventors Alexander Kalnitsky et al., entitled "SELF-ALIGNED NPN TRANSISTOR WITH RAISED EXTRINSIC BASE", now U.S. Pat. No. 6,767,798, which are both of which are assigned to Maxim Integrated Products, Inc."

Paragraph number 0029, please replace the paragraph thereat with the amended paragraph as follows:

"Figure 3E illustrates a cross-sectional view of the exemplary semiconductor device 100 at another subsequent step of the exemplary method of forming a bipolar transistor in accordance with the invention. In this subsequent step, a thin nitride spacer 132 adjacent to the polysilicon emitter 130 is formed by depositing a layer of silicon nitride 134 having a thickness in the range of 0.01 microns to 0.1 microns and ~~isotropically~~ anisotropically etching the layers of silicon nitride 134. In the exemplary method, the silicon nitride layers 120, 134 are directionally etched with a plasma etcher."